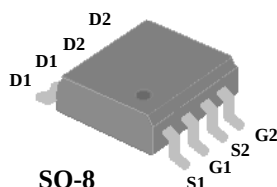


- ▼ Low Gate Charge
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free

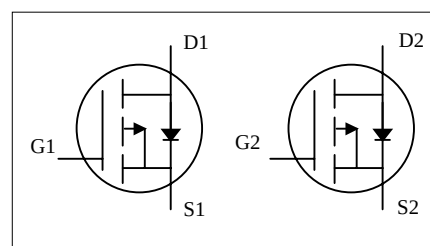


BV_{DSS}	-30V
$R_{DS(ON)}$	20m Ω
I_D^3	-8.3A

Description

XP3B020 series are innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The SO-8 package is widely preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	+20	V
$I_D@T_A=25^\circ\text{C}$	Drain Current ³ , V_{GS} @ 10V	-8.3	A
$I_D@T_A=70^\circ\text{C}$	Drain Current ³ , V_{GS} @ 10V	-6.6	A
I_{DM}	Pulsed Drain Current ¹	-30	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	2	W
E_{AS}	Single Pulse Avalanche Energy ⁴	16.2	mJ
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_j	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-8A	-	-	20	mΩ
		V _{GS} =-4.5V, I _D =-4A	-	-	36	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-8A	-	16	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	-	-	-10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =-5A	-	12	19.2	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V	-	4.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	4	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-15V	-	11	-	ns
t _r	Rise Time	I _D =-1A	-	7	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	43	-	ns
t _f	Fall Time	V _{GS} =-10V	-	20	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1300	2080	pF
C _{oss}	Output Capacitance	V _{DS} =-15V	-	190	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	135	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-1.7A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	I _S =-8A, V _{GS} =0V,	-	12	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=-100A/μs	-	5	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t ≤ 10s ; 135 °C/W when mounted on Min. copper pad.
- 4.Starting T_j=25°C , V_{DD}=-30V , L=0.1mH , R_G=25Ω

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT, AUTOMOTIVE OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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XSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

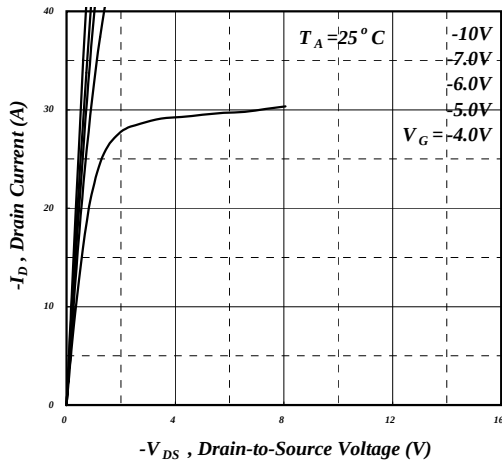


Fig 1. Typical Output Characteristics

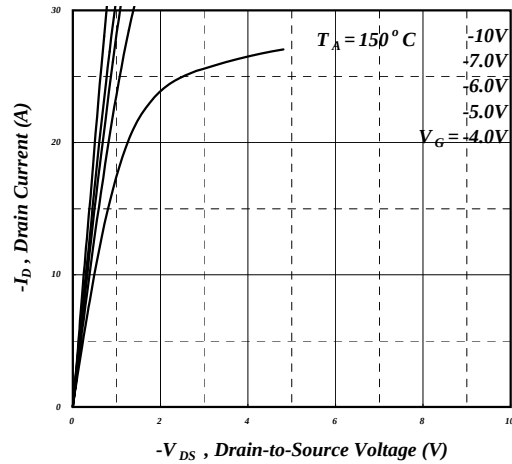


Fig 2. Typical Output Characteristics

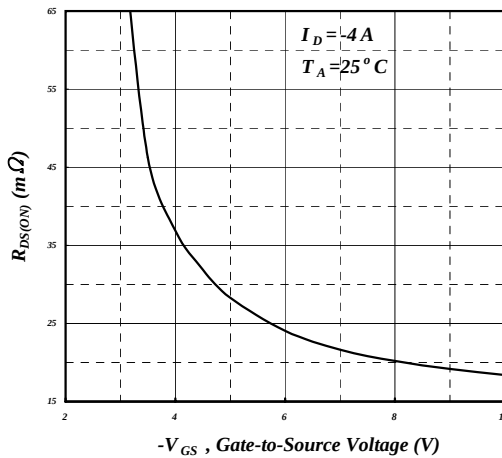
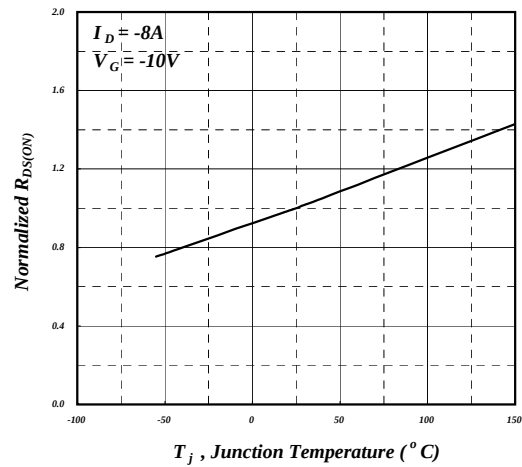
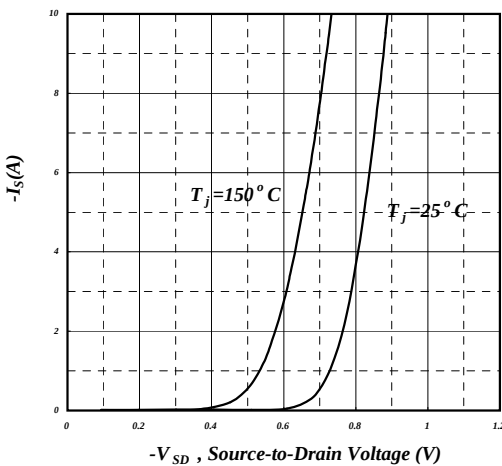


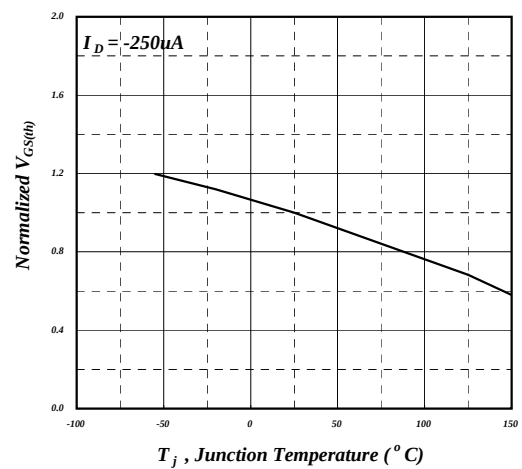
Fig 3. On-Resistance v.s. Gate Voltage



**Fig 4. Normalized On-Resistance
v.s. Junction Temperature**



**Fig 5. Forward Characteristic of
Reverse Diode**



**Fig 6. Gate Threshold Voltage v.s.
Junction Temperature**

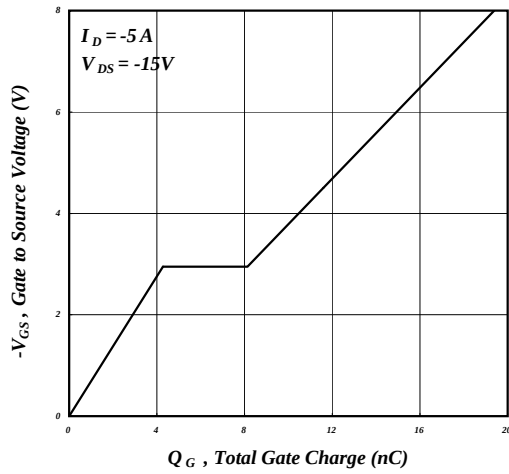


Fig 7. Gate Charge Characteristics

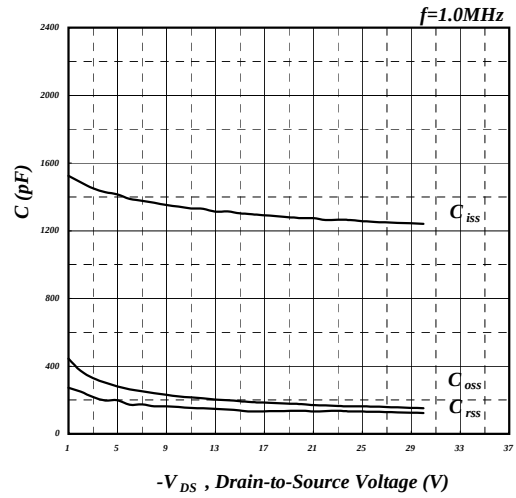


Fig 8. Typical Capacitance Characteristics

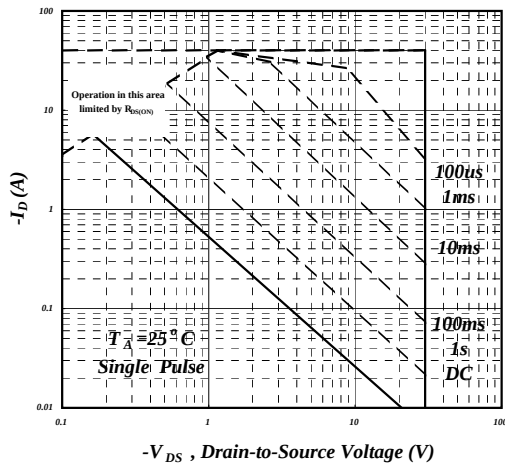


Fig 9. Maximum Safe Operating Area

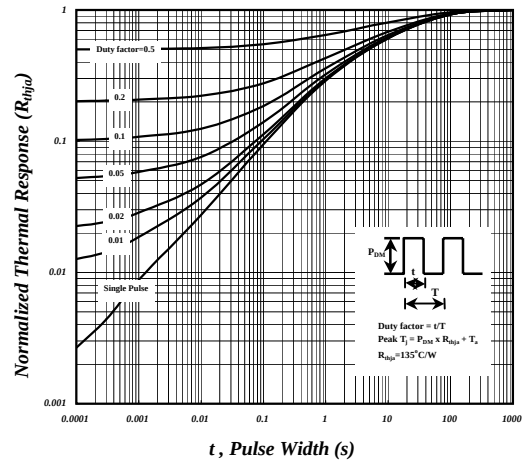


Fig 10. Effective Transient Thermal Impedance

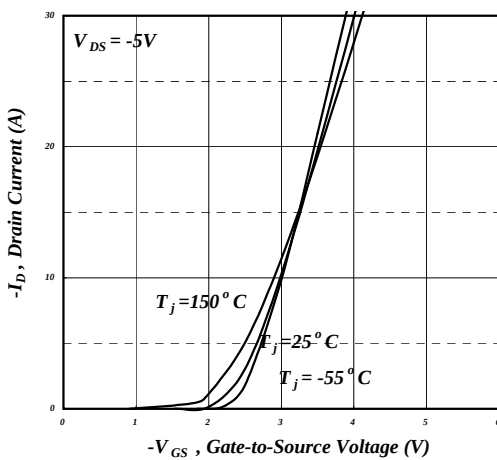


Fig 11. Transfer Characteristics

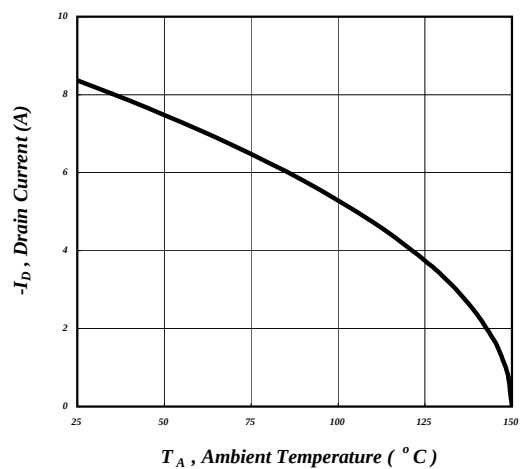


Fig 12. Drain Current v.s. Ambient Temperature

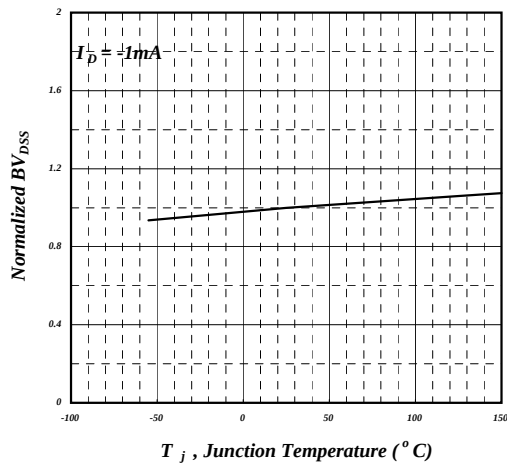


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

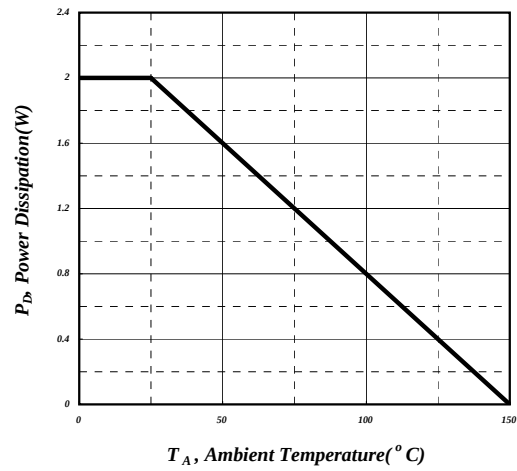


Fig 14. Total Power Dissipation

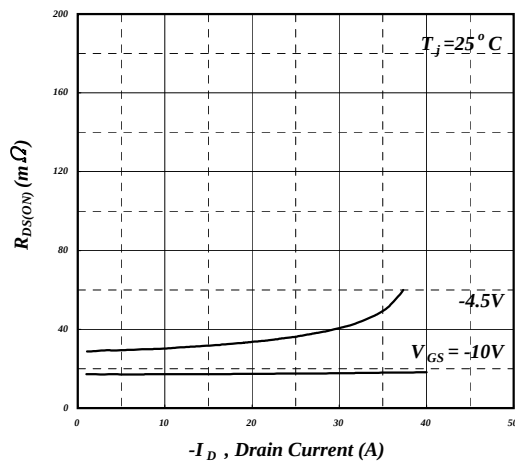
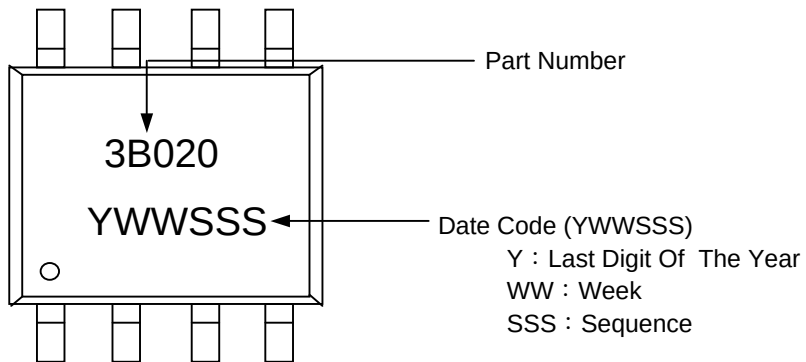
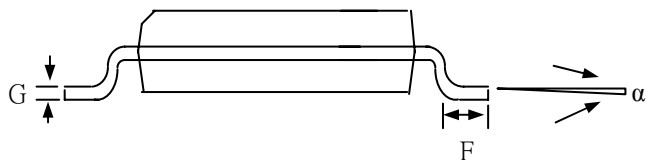
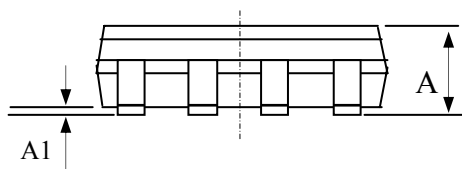
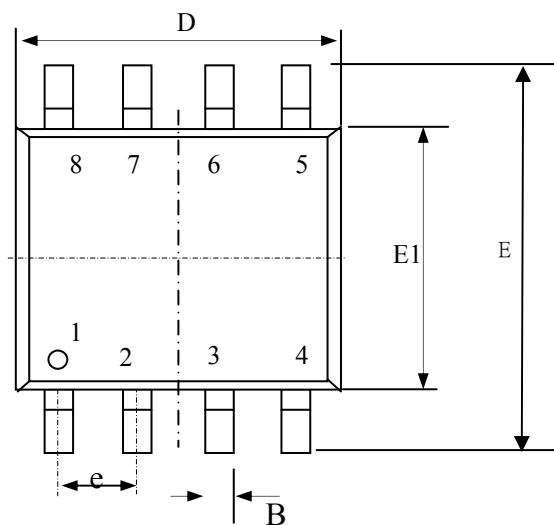


Fig 15. Typ. Drain-Source on State Resistance

MARKING INFORMATION



Package Outline : SO-8



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.05	0.15	0.25
B	0.30	0.41	0.51
D	4.80	5.05	5.30
E	5.79	6.00	6.20
E1	3.70	3.90	4.10
e	1.27 TYP		
G	0.17	0.21	0.25
F	0.38	0.83	1.27
α	0°	4°	8°

- 1.All Dimension Are In Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.

SO-8 FOOTPRINT :

